TOSHIBA PHOTOCOUPLER GaAIAs IRED + PHOTO-IC

Preliminary

TLP719

DIGITAL LOGIC GROUND ISOLATION.

LINE RECEIVER.

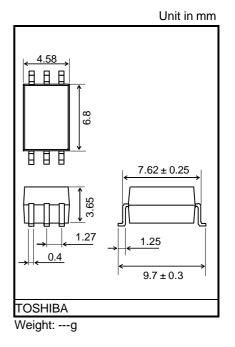
MICROPROCESSOR SYSTEM INTERFACES.
SWITCHING POWER SUPPLY FEEDBACK CONTROL.
TRANSISTOR INVERTOR.

The TOSHIBA TLP719 consists of a GaAlAs high-output light emitting diode and a high speed detector.

This unit is 6-lead SDIP. TLP719 is 50% smaller than 8PIN DIP and has suited the safety standard reinforced insulation class. So mounting area in safety standard required equipment can be reduced.

TLP719 has a Faraday shield integrated on the photodetector chip provides an effective common mode noise transient immunity.

So this is suitable for application in noisy environmental condition.



- Open Collector
- Package Type : SDIP6
- Isolation voltage : 5000 Vrms (Min.)
- Common mode Transient Immunity

: ±10kV/us(Min.) @VCM=400V

• Switching speed : t_{pHL} = 0.8µs , t_{pLH} = 0.8µs (Max.)

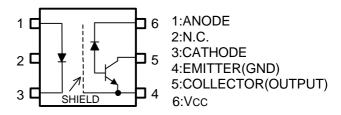
@ $I_F = 16mA$, $V_{CC} = 5V$,

 $R_L = 1.9kO$, Ta = 25°C

- TTL Compatible
- Construction Mechanical Rating

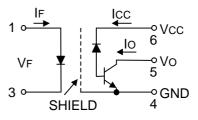
	7.62 mm pich standard type	10.16 mm pich TLPXXXF type
Creepage Distance	7.0 mm (Min)	8.0 mm (Min)
Clearance	7.0 mm (Min)	8.0 mm (Min)
Insulation Thickness	0.4 mm (Min)	0.4 mm (Min)

PIN CONFIGURATION (Top view)



SCHEMATIC

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A 0.1µF bypass capacitor must be connected between pins 4 and 6.

Maximum Ratings (Ta = 25°C)

	Characteristic		Symbol	Rating	Unit
	Forward current	(Note 1)	lF	25	mA
	Pulse forward current	(Note 2)	IFP	50	mA
LED	Peak transient forward current	(Note 3)	I _{FPT}	1	А
۳	Reverse voltage		V _R	5	V
	Diode power dissipation	(Note 4)	P_{D}	45	mW
	Junction Temperature		Tj	125	°C
	Output current		ΙO	8	mA
	Peak output current		I _{OP}	16	mA
Detector	Output voltage		Vo	-0.5~20	V
Dete	Supply voltage		V _{CC}	-0.5~30	V
	Output power dissipation	(Note 5)	PO	100	mW
	Junction Temperature		Tj	125	°C
Оре	erating temperature range		T _{opr}	-55~100	°C
Storage temperature range			T _{opr}	-55~125	°C
Lead solder temperature (10s)			T _{sol}	260	°C
	ation voltage , 1min., R.H.= 60%)	(Note 6)	BVS	5000	Vrms

(Note 1) Derate 0.45mA / °C above 70°C.

(Note 2) 50% duty cycle, 1ms pulse width. Derate 0.9mA / °C above 70°C.

(Note 3) Pulse width = 1μ s, 300pps.

(Note 4) Derate 0.8mW / °C above 70°C.

(Note 5) Derate 1.8mW / °C above 70°C.

(Note 6) Device considered a two terminal device: Pins 1, 2 and 3 shorted together and pins 4, 5 and 6 shorted together.



Electrical Characteristics (Ta = 25°C)

	Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
	Forward voltage	V _F	I _F = 16mA		1.65	1.85	V
۵	Forward voltage Temperature coefficient	?V _F /?Ta	I _F = 16mA	?	-2	?	mV / °C
Ē	Reverse current	I _R	V _R = 5V	?	?	10	μΑ
	Capacitance between terminal	C _T	V _F = 0V , f = 1MHz	?	45	?	pF
High level output cu		I _{OH (1)}	$I_F = 0mA$, $V_{CC} = V_O = 5.5V$?	3	500	nA
	High level output current	I _{OH} (2)	I _F = 0mA ,V _{CC} = 30V V _O = 20V	?	?	5	μΑ
		ГОН	I _F = 0mA ,V _{CC} = 30V V _O = 20V,Ta = 70°C	?	?	50	μΛ
De	High level supply voltage	Іссн	I _F = 0mA ,V _{CC} = 30V	?	0.01	1	μΑ
	Supply voltage	Vcc	I _{CC} = 0.01mA	30	?	?	V
	Output voltage	Vo	I _O = 0.5mA	20	?	?	V

Coupled Electrical Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
Current transfer ratio	I _O / I _F	$I_F = 16 \text{mA}$, $V_{CC} = 4.5 \text{V}$ $V_O = 0.4 \text{V}$	20	?	?	%
Low level output voltage	V _{OL}	I _F = 16mA ,V _{CC} = 4.5V I _O = 2.4mA	?	?	0.4	V

Isolation Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
Capacitance input to output	CS	V = 0V, $f = 1MHz$ (Note 6)	?	0.8	?	pF
Isolation resistance	R _S	R.H. = 60% , $V_S = 500V$ (Note 6)	1×10 ¹²	10 ¹⁴	?	0
Isolation voltage	BVS	AC,1 minute	5000	?	?	\/
		AC,1 second , in oil	?	10000	?	V _{rms}
		DC,1 minute , in oil	?	10000	?	Vdc

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Switching Characteristics (Ta = 25°C, Vcc = 5V)

Characteristic		Symbol	Test Cir- cuit	Test Condition	Min.	Тур.	Max.	Unit
Propagation delay time	(H? L)	t _{pHL}	Fig1	I _F = 0? 16mA R _L = 1.9kO	?	?	0.8	μs
Propagation delay time	(L? H)	t _{pLH}		I _F = 16? 0mA R _L = 1.9kO	?	?	0.8	μs
Common mode transient immunity at logic high output	(Note 7)	CM _H	Fig2	$I_F = 0 \text{mA}$, $V_{CM} = 400 V_{p-p}$ $R_L = 1.9 \text{kO}$	10000	?	?	V/µs
Common mode transient immunity at logic low output	(Note 7)	CML		$I_F = 16 \text{mA} , V_{CM} = 400 V_{p-p}$ $R_L = 1.9 \text{kO}$	-10000	?	?	V / µs

(Note 7) : CM_L is the maximum rate of fall of the common mode voltage that can be sustained with the output voltage in the logic low state($V_O < 0.8V$). CM_H is the maximum rate of rise of the common mode voltage that can be sustained with the output voltage in the logic high state($V_O > 2V$).

Fig 1.Switching Time Test Circuit

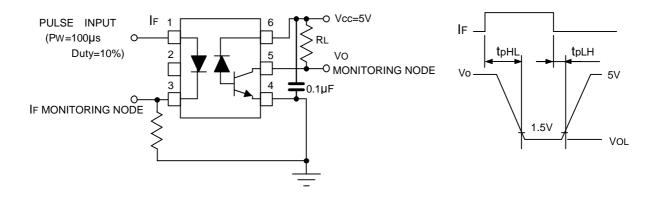
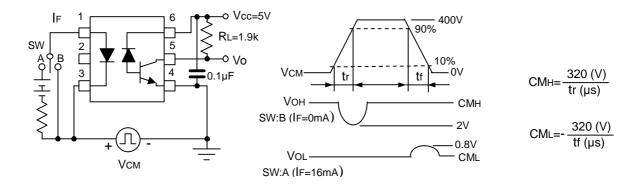


Fig 2.Common Mode Noise Immunity Test Circuit.



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